

EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S1	378	((rotating rotatable moving near5 (linear\$4 cyclic repeated\$3 sequential\$4)) near5 (platen platform substrate) carrousel) and thin adj2 film and (vaporize evaporate vaporization evaporation gaseous) with (source target metal\$4 magnesium niobium tin titanium zinc cadmium) and ((several multiple seperate sequential) near5 (target deposit\$4) and reaction deposit \$4 near5 (zone chamber room substrate) and reaction near5 (zone chamber room)) and (RF electron laser sputter\$4) and (vacuum pressure torr pa kpa)	US-PGPUB; USPAT; USOCR	OR	ON	2008/04/27 12:46
S2	288	S1 and (superconductor semiconductor CdSe ZnSe CdS ZnS TiB alloy NbTi Nb\$Ti "Nb.sub.3 Sn" oxide HTS YBCO BSSCO "MgB.sub.2" MgB2 magnesium adj \$2boride) near5 (thin film)	US-PGPUB; USPAT; USOCR	OR	ON	2008/04/27 12:47
S3	26	S2 and (as\$2grown in\$2situ in\$2place) with (superconductor semiconductor CdSe ZnSe TiB CdS alloy NbTi Nb\$Ti "Nb.sub.3 Sn" oxide HTS YBCO BSSCO "MgB.sub.2" MgB2 magnesium adj \$2boride thin adj2 film)	US-PGPUB; USPAT; USOCR	OR	ON	2008/04/27 12:47
S4	5	S2 and ("MgB.sub.2" MgB2 magnesium adj \$2boride)	US-PGPUB; USPAT; USOCR	OR	ON	2008/04/27 12:47
S5	13	S2 and (Mg magnesium) near5 (gas vapor vapour plume)	US-PGPUB; USPAT; USOCR	OR	ON	2008/04/27 12:47
S6	110	S2 and wafer with substrate	US-PGPUB; USPAT; USOCR	OR	ON	2008/04/27 12:48
S7	100	S2 and evaporat\$4 with electron adj beam	US-PGPUB; USPAT; USOCR	OR	ON	2008/04/27 12:48
S8	137	S2 and (Mg magnesium metal\$4 zinc cadmium niobium titanium tin) near5 (gas vapor vapour plume)	US-PGPUB; USPAT; USOCR	OR	ON	2008/04/27 12:49
S9	203	S2 and deposit\$4 near5 (zone chamber room substrate) and reaction near5 (zone chamber room)	US-PGPUB; USPAT; USOCR	OR	ON	2008/04/27 12:49
S10	112	S9 and (divid\$4 separat\$4 wall) near5 (chamber room zone)	US-PGPUB; USPAT; USOCR	OR	ON	2008/04/27 12:49
S11	92	S8 and S9	US-PGPUB; USPAT; USOCR	OR	ON	2008/04/27 12:50
S12	72	S8 and S10	US-PGPUB; USPAT; USOCR	OR	ON	2008/04/27 12:51

S13	28	S8 and (505/452,470,473-476,480,718,730-732,758,826,950.ccls. 427/62,117,126.1,126.3,294,314,537,546,561,576,592-593,597,255.S29. ccls. 204/470,473,192.1,192.15,192.24,192.25.ccls. 118/719,730.ccls. 29/599.ccls. 117/101.ccls. 438/758.ccls.)	US-PGPUB; USPAT; USOCR	OR	ON	2008/04/27 12:52
S14	189	(as\$2grown in\$2situ in\$2place) with (superconductor semiconductor CdSe ZnSe TiB CdS alloy NbTi Nb\$Ti "Nb.sub.3 Sn" oxide HTS YBCO BSSCO "MgB. sub.2" MgB2 magnesium adj \$2boride) with thin adj2 film	US-PGPUB; USPAT; USOCR	OR	ON	2008/04/27 12:52
S15	14	S14 and ((rotating rotatable moving near5 (linear\$4 cyclic repeated\$3 sequential\$4)) near5 (platen platform substrate sample target) carrousel)	US-PGPUB; USPAT; USOCR	OR	ON	2008/04/27 12:54
S16	5	((rotating rotatable) near5 (platen substrate platform) carrousel).clm. and film.clm. and (superconductor semiconductor CdS ZnS ZnSe CdSe TiB Nb\$Ti "Nb.sub.3 Sn" alloy HTS YBCO BSSCO "MgB.sub.2" MgB2 magnesium adj \$2boride).clm. and (metal\$4 magnesium Mg zinc niobium titanium zinc cadmium) near5 (gas gaseous vaporized vapor vapour).clm. and (deposition substrate).clm. and reaction.clm.	US-PGPUB; USPAT; USOCR	OR	ON	2008/04/27 12:55
S17	19	(as\$2grown in\$2situ in\$2place) with (superconductor alloy ZnSe CdSe CdS NbTi Nb3Sn HTS YBCO BSSCO MgB2 magnesium adj \$2boride carbide nitride boride) same (thin adj film)	FPRS; EPO; JPO; DERWENT	OR	ON	2008/04/27 12:55
S18	3	(as\$2grown in\$2situ in\$2place) and (superconductor alloy NbTi Nb3Sn HTS YBCO BSSCO MgB2 magnesium adj \$2boride oxide) and (thin adj film) and rotat\$5	FPRS; EPO; JPO; DERWENT	OR	ON	2008/04/27 12:56
S19	3	(mockley near2 brian ruby near2 ward).in.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2008/04/27 12:56
S20	7	((mockley near2 brian ruby near2 ward).in. Conductus.as.) and (superconductor and thin adj film) and (metal\$4 magnesium) near5 (vapor gas gaseous)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2008/04/27 12:56
S21	41	((mockley near2 brian ruby near2 ward).in. Conductus.as.) and (superconductor and thin adj film)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2008/04/27 12:56
S22	11	("5116807" "5841342" "5350739" "6514557" "5423914" "20010036214" "6626995" "4851095" "20030073324" "6527866" "5674813").did.	US-PGPUB; USPAT; USOCR	OR	ON	2008/04/27 12:56

S23	25	(trace\$2 negligible) with ppm with oxygen and vacuum and (metal semiconductor superconductor) with thin adj2 film	US-PGPUB; USPAT	OR	ON	2008/04/27 12:57
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4/27/2008 12:58:18 PM

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